



Is Now Part of



ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at
www.onsemi.com

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

**N-Channel Logic Level Power MOSFET
100 V, 12 A, 200 mΩ**

These are N-Channel enhancement mode silicon gate power field effect transistors specifically designed for use with logic level (5V) driving sources in applications such as programmable controllers, automotive switching and solenoid drivers. This performance is accomplished through a special gate oxide design which provides full rated conduction at gate biases in the 3V to 5V range, thereby facilitating true on-off power control directly from logic circuit supply voltages.

Formerly developmental type TA09526.

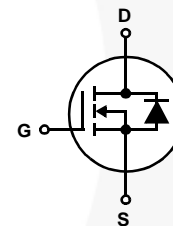
Ordering Information

PART NUMBER	PACKAGE	BRAND
RFP12N10L	TO-220AB	F12N10L

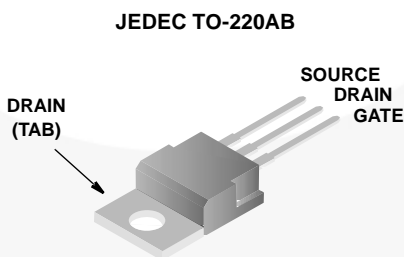
Features

- 12A, 100V
- $r_{DS(ON)} = 0.200\Omega$
- Design Optimized for 5V Gate Drives
- Can be Driven Directly from QMOS, NMOS, TTL Circuits
- Compatible with Automotive Drive Requirements
- SOA is Power-Dissipation Limited
- Nanosecond Switching Speeds
- Linear Transfer Characteristics
- High Input Impedance
- Majority Carrier Device
- Related Literature
 - TB334 "Guidelines for Soldering Surface Mount Components to PC Boards"

Symbol



Packaging



RFP12N10L

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, Unless Otherwise Specified

	RFP12N10L	UNITS
Drain to Source Voltage (Note 1)	V_{DS}	100 V
Drain to Gate Voltage ($R_{GS} = 1\text{M}\Omega$) (Note 1)	V_{DGR}	100 V
Continuous Drain Current	I_D	12 A
Pulsed Drain Current (Note 3)	I_{DM}	30 A
Gate to Source Voltage	V_{GS}	± 10 V
Maximum Power Dissipation	P_D	60 W
Above $T_C = 25^\circ\text{C}$, Derate Linearly		0.48 W/ $^\circ\text{C}$
Operating and Storage Temperature	T_J, T_{STG}	-55 to 150 $^\circ\text{C}$
Maximum Temperature for Soldering		
Leads at 0.063in (1.6mm) from Case for 10s	T_L	300 $^\circ\text{C}$
Package Body for 10s, See Techbrief 334	T_{pkg}	260 $^\circ\text{C}$

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

1. $T_J = 25^\circ\text{C}$ to 125°C .

Electrical Specifications $T_C = 25^\circ\text{C}$, Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Drain to Source Breakdown Voltage	BV_{DSS}	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	100	-	-	V
Gate to Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$ (Figure 7)	1	-	2	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 80\text{V}$	-	-	1	μA
		$V_{GS} = 0\text{V}$ $T_C = 125^\circ\text{C}$	-	-	50	μA
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = 10\text{V}, V_{DS} = 0\text{V}$	-	-	100	nA
Drain to Source On Resistance (Note 2)	$r_{DS(ON)}$	$I_D = 12\text{A}, V_{GS} = 5\text{V}$ (Figures 5, 6)	-	-	0.200	Ω
Input Capacitance	C_{ISS}	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$ (Figure 8)	-	-	900	pF
Output Capacitance	C_{OSS}		-	-	325	pF
Reverse-Transfer Capacitance	C_{RSS}		-	-	170	pF
Turn-On Delay Time	$t_{d(ON)}$	$I_D = 6\text{A}, V_{DD} = 50\text{V}, R_G = 6.25\Omega,$ $V_{GS} = 5\text{V}$ (Figures 9, 10, 11)	-	15	50	ns
Rise Time	t_r		-	70	150	ns
Turn-Off Delay Time	$t_{d(OFF)}$		-	100	130	ns
Fall Time	t_f		-	80	150	ns
Thermal Resistance Junction to Case	$R_{\theta JC}$	TO-220			2.083	$^\circ\text{C/W}$

Source to Drain Diode Specifications

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Source to Drain Diode Voltage (Note 2)	V_{SD}	$I_{SD} = 6\text{A}$	-	-	1.4	V
Diode Reverse Recovery Time	t_{rr}	$I_{SD} = 4\text{A}, dI_{SD}/dt = 50\text{A}/\mu\text{s}$	-	150	-	ns

NOTES:

2. Pulsed: pulse duration = $80\mu\text{s}$ max, duty cycle = 2%.
3. Repetitive rating: pulse width limited by maximum junction temperature.

Typical Performance Curves Unless Otherwise Specified

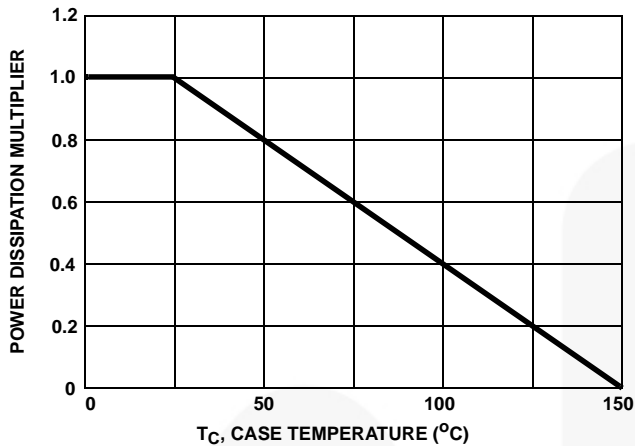


FIGURE 1. NORMALIZED POWER DISSIPATION vs CASE TEMPERATURE

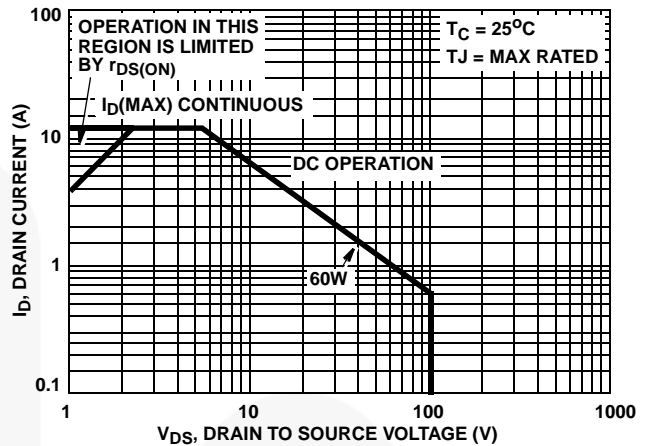


FIGURE 2. FORWARD BIAS OPERATING AREA

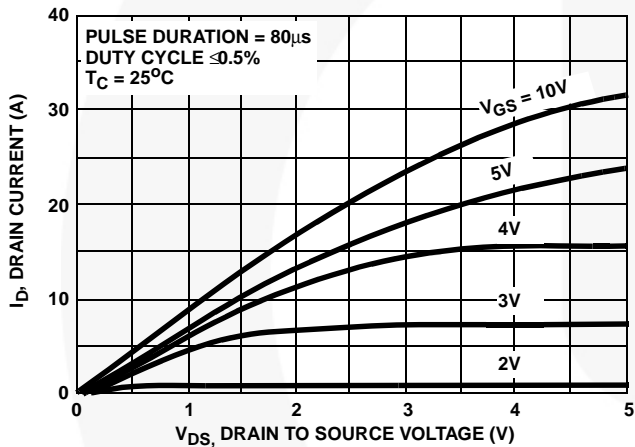


FIGURE 3. SATURATION CHARACTERISTICS

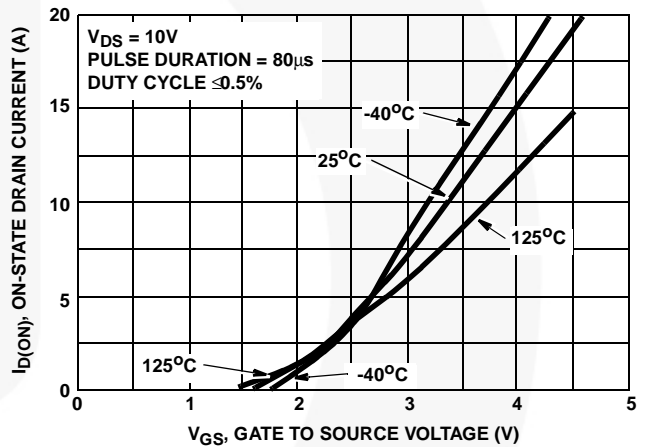


FIGURE 4. TRANSFER CHARACTERISTICS

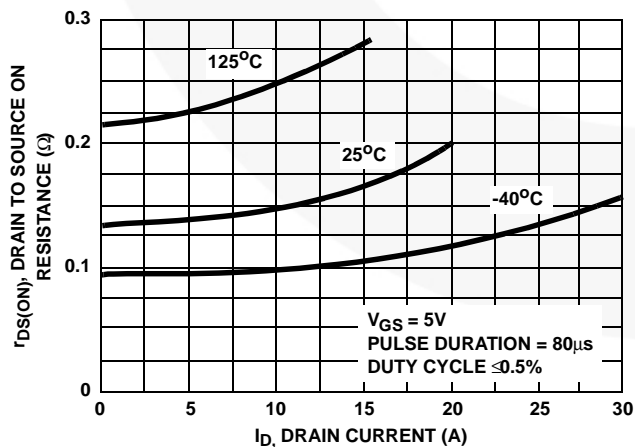


FIGURE 5. DRAIN TO SOURCE ON RESISTANCE vs DRAIN CURRENT

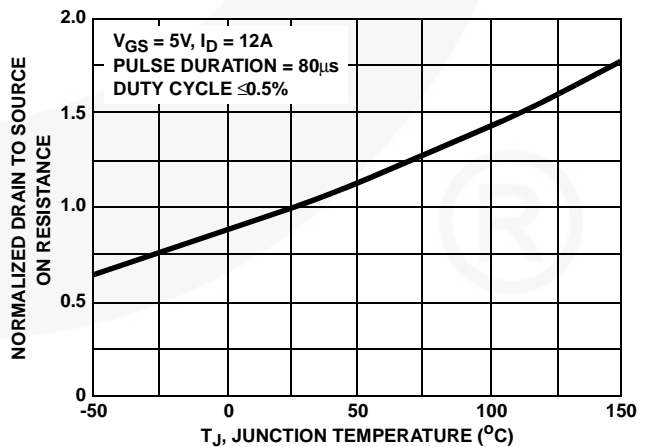


FIGURE 6. NORMALIZED DRAIN TO SOURCE ON RESISTANCE vs JUNCTION TEMPERATURE

Typical Performance Curves Unless Otherwise Specified (Continued)

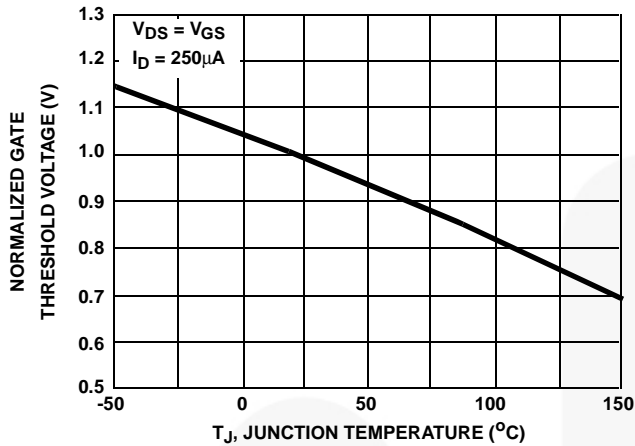


FIGURE 7. NORMALIZED GATE THRESHOLD VOLTAGE vs JUNCTION TEMPERATURE

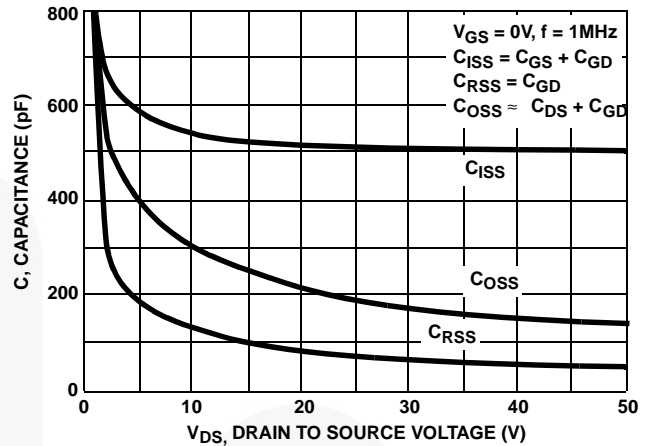
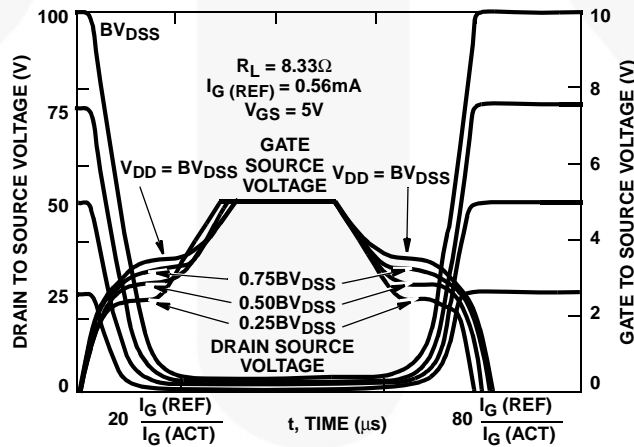


FIGURE 8. CAPACITANCE vs DRAIN TO SOURCE VOLTAGE



NOTE: Refer to Fairchild Applications Notes AN7254 and AN7260

FIGURE 9. NORMALIZED SWITCHING WAVEFORMS FOR CONSTANT GATE CURRENT

Test Circuits and Waveforms

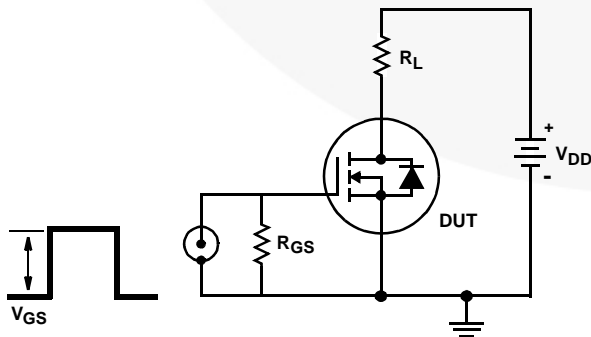


FIGURE 10. SWITCHING TIME TEST CIRCUIT

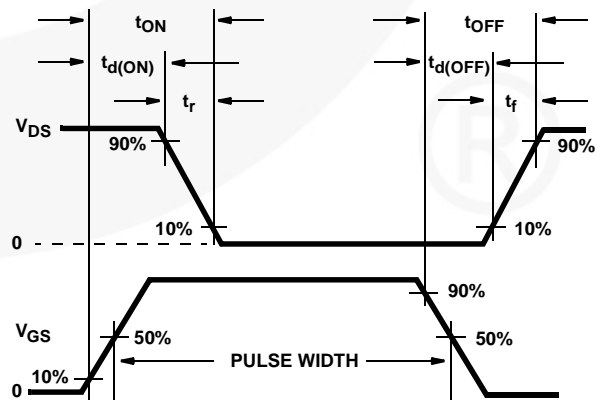


FIGURE 11. RESISTIVE SWITCHING WAVEFORMS

Test Circuits and Waveforms (Continued)

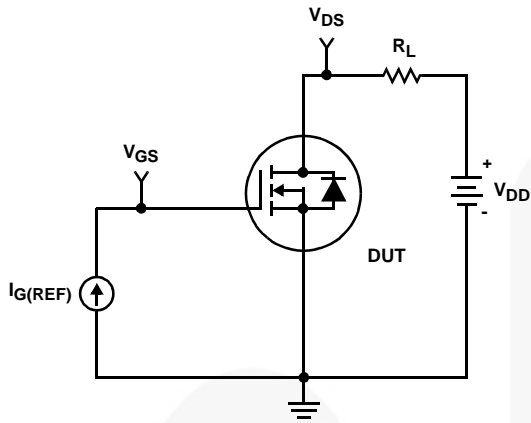


FIGURE 12. GATE CHARGE TEST CIRCUIT

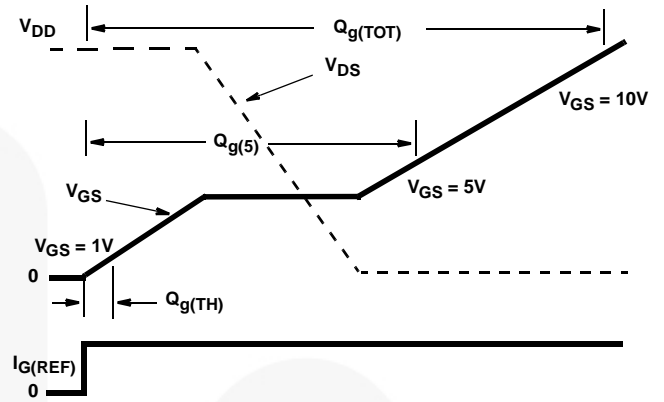




FIGURE 13. GATE CHARGE WAVEFORMS





TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

AccuPower™	F-PFS™	PowerTrench®	Sync-Lock™
AX-CAP®*	FRFET®	PowerXS™	SYSTEM GENERAL®*
BitSiC™	Global Power Resource™	Programmable Active Droop™	TinyBoost®
Build it Now™	GreenBridge™	QFET®	TinyBuck®
CorePLUS™	Green FPS™	QS™	TinyCalc™
CorePOWER™	Green FPS™ e-Series™	Quiet Series™	TinyLogic®
CROSSVOLT™	Gmax™	RapidConfigure™	TINYOPTO™
CTL™	GTO™	Saving our world, 1mW/W/kW at a time™	TinyPower™
Current Transfer Logic™	IntelliMAX™	SignalWise™	TinyPWM™
DEUXPEED®	ISOPLANAR™	SmartMax™	TinyWire™
Dual Cool™	Marking Small Speakers Sound Louder and Better™	SMART START™	TranSiC™
EcoSPARK®	MegaBuck™	Solutions for Your Success™	TriFault Detect™
EfficientMax™	MICROCOUPLER™	SPM®	TRUECURRENT®*
ESBC™	MicroFET™	STEALTH™	µSerDes™
 Fairchild®	MicroPak™	SuperFET®	 SerDes™
Fairchild Semiconductor®	MicroPak2™	SuperSOT™-3	UHC®
FACT Quiet Series™	MillerDrive™	SuperSOT™-6	Ultra FRFET™
FACT®	MotionMax™	SuperSOT™-8	UniFET™
FAST®	mWSaver®	SupreMOS®	VCX™
FastvCore™	OptoHiT™	SyncFET™	VisualMax™
FETBench™	OPTOLOGIC®		VoltagePlus™
FPS™	OPTOPLANAR®		XS™

*Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used here in:

- Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.Fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufacturers of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed application, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handling and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address and warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev. 166